



BG5(BZG5)

GLASS PASSIVATED SILICON FAST RECOVERY DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.



Use for high-frequency,switch circuit.

Store temperature: -55~+150°C

Quality Class: JP, JT, JCT, GS, G, G+

Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications	Test Condition
Peak Repetitive Reverse Voltage	V_{RRM}	V	50~1200	
Average Forward Current	$I_{F(AV)}$	A	5.0	
Peak Forward Voltage	V_{FM}	V	2.2	$I=I_{F(AV)}$
Average Forward Voltage	V_F	V	1.2	$I=I_{F(AV)}$
Non-repeat Forward Surge Current	I_{FSM}	A	60	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I_{RM1}	uA	10	$V_R=V_{RRM}, T_a=25^\circ C$
Peak Reverse Current	I_{RM2}	uA	200	$V_R=V_{RRM}, T_a=125^\circ C$
Junction Temperature	T_{jm}	°C	150	
Reverse Recovery Time	t_{rr}	uS	1	$V_R=10V, I_F=50mA, R_L=75ohms$

SPECIFICATIONS:

A	B	C	D	E	F	G	H	I
50V	100V	200V	300V	400V	600V	800V	1000V	1200V

Outline and Dimensions: